

# IRG4IBC30FD

INSULATED GATE BIPOLAR TRANSISTOR WITH  
ULTRAFAST SOFT RECOVERY DIODE

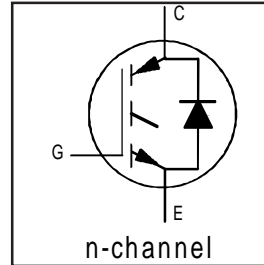
Fast CoPack IGBT

## Features

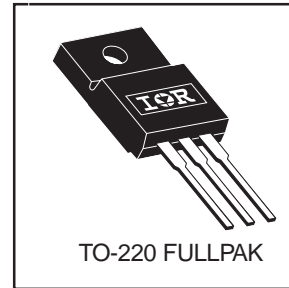
- Very Low 1.59V voltage drop
- 2.5kV, 60s insulation voltage <sup>Ⓢ</sup>
- 4.8 mm creepage distance to heatsink
- Fast: Optimized for medium operating frequencies ( 1-5 kHz in hard switching, >20 kHz in resonant mode).
- IGBT co-packaged with HEXFRED™ ultrafast, ultrasoft recovery antiparallel diodes
- Tighter parameter distribution
- Industry standard Isolated TO-220 Fullpak™ outline

## Benefits

- Simplified assembly
- Highest efficiency and power density
- HEXFRED™ antiparallel Diode minimizes switching losses and EMI



$V_{CES} = 600V$
$V_{CE(on) typ.} = 1.59V$
@ $V_{GE} = 15V, I_C = 17A$



## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	20.3	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	11	
$I_{CM}$	Pulsed Collector Current <sup>①</sup>	120	
$I_{LM}$	Clamped Inductive Load Current <sup>②</sup>	120	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	8.5	
$I_{FM}$	Diode Maximum Forward Current	120	
$V_{isol}$	RMS Isolation Voltage, Terminal to Case <sup>Ⓢ</sup>	2500	V
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	45	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	18	
$T_J$	Operating Junction and	-55 to +150	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

## Thermal Resistance

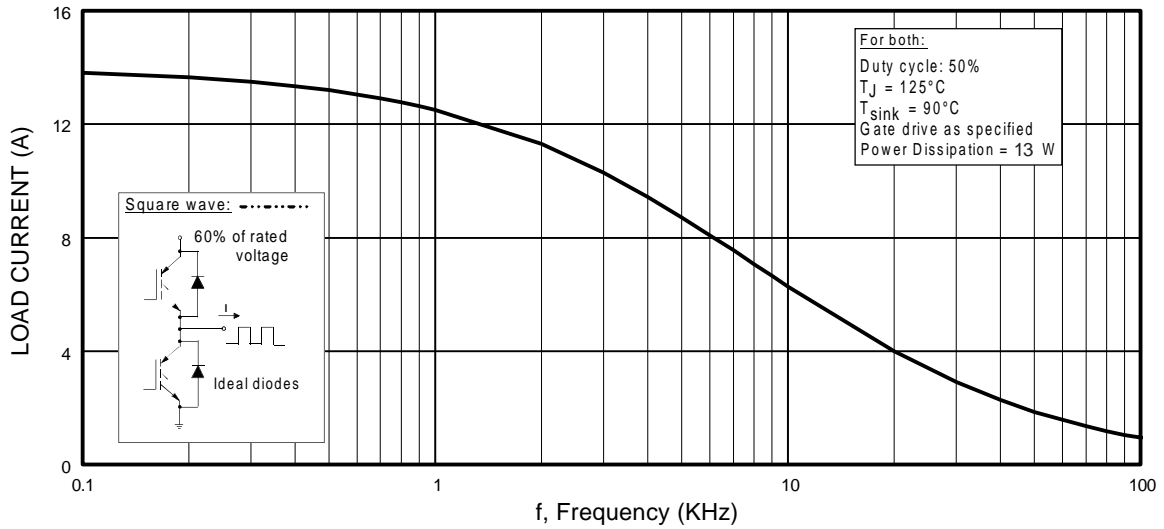
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	2.8	°C/W
$R_{\theta JC}$	Junction-to-Case - Diode	—	4.1	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	65	
$Wt$	Weight	2.0 (0.07)	—	g (oz)

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

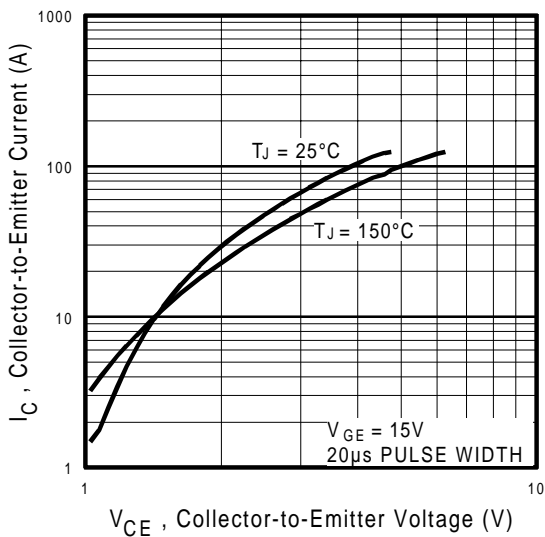
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage <sup>③</sup>	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.69	—	V/°C	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.59	1.8	V	$I_C = 17A$ $V_{GE} = 15V$ $I_C = 31A$ $V_{GE} = 15V$ $I_C = 17A, T_J = 150^\circ\text{C}$ See Fig. 2, 5
		—	1.99	—		
		—	1.70	—		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$
$g_{fe}$	Forward Transconductance <sup>④</sup>	6.1	10	—	S	$V_{CE} = 100V, I_C = 17A$
$I_{CES}$	Zero Gate Voltage Collector Current	—	—	250	$\mu A$	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	2500		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
$V_{FM}$	Diode Forward Voltage Drop	—	1.4	1.7	V	$I_C = 12A$ $V_{GE} = 15V$ $I_C = 12A, T_J = 150^\circ\text{C}$ See Fig. 13
		—	1.3	1.6		
$I_{GES}$	Gate-to-Emitter Leakage Current	—	—	$\pm 100$	nA	$V_{GE} = \pm 20V$

## Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

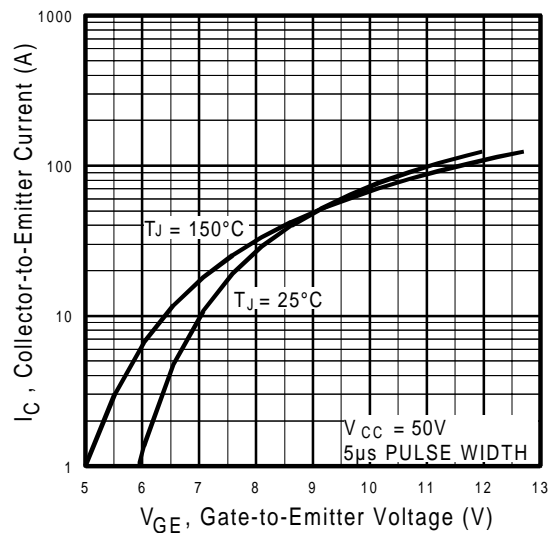
	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge (turn-on)	—	51	77	nC	$I_C = 17A$ $V_{CC} = 400V$ $V_{GE} = 15V$ See Fig. 8
$Q_{ge}$	Gate - Emitter Charge (turn-on)	—	7.9	12		
$Q_{gc}$	Gate - Collector Charge (turn-on)	—	19	28		
$t_{d(on)}$	Turn-On Delay Time	—	42	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 17A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 23\Omega$ Energy losses include "tail" and diode reverse recovery. See Fig. 9, 10, 11, 18
$t_r$	Rise Time	—	26	—		
$t_{d(off)}$	Turn-Off Delay Time	—	230	350		
$t_f$	Fall Time	—	160	230	mJ	$T_J = 150^\circ\text{C}$ , $I_C = 17A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 23\Omega$ Energy losses include "tail" and diode reverse recovery. See Fig. 9, 10, 11, 18
$E_{on}$	Turn-On Switching Loss	—	0.63	—		
$E_{off}$	Turn-Off Switching Loss	—	1.39	—		
$E_{ts}$	Total Switching Loss	—	2.02	3.9	mJ	$T_J = 150^\circ\text{C}$ , $I_C = 17A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 23\Omega$ Energy losses include "tail" and diode reverse recovery. See Fig. 9, 10, 11, 18
$t_{d(on)}$	Turn-On Delay Time	—	42	—		
$t_r$	Rise Time	—	27	—		
$t_{d(off)}$	Turn-Off Delay Time	—	310	—	nH	Measured 5mm from package
$t_f$	Fall Time	—	310	—		
$E_{ts}$	Total Switching Loss	—	3.2	—		
$L_E$	Internal Emitter Inductance	—	7.5	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$ See Fig. 7
$C_{ies}$	Input Capacitance	—	1100	—		
$C_{oes}$	Output Capacitance	—	74	—		
$C_{res}$	Reverse Transfer Capacitance	—	14	—	ns	$T_J = 25^\circ\text{C}$ $I_F = 12A$ $T_J = 125^\circ\text{C}$ 14 $V_R = 200V$
$t_{rr}$	Diode Reverse Recovery Time	—	42	60		
		—	80	120		
$I_{rr}$	Diode Peak Reverse Recovery Current	—	3.5	6.0	A	$T_J = 25^\circ\text{C}$ $I_F = 12A$ $T_J = 125^\circ\text{C}$ 15 $V_R = 200V$
		—	5.6	10		
$Q_{rr}$	Diode Reverse Recovery Charge	—	80	180		
		—	220	600	nC	$T_J = 25^\circ\text{C}$ $I_F = 12A$ $T_J = 125^\circ\text{C}$ 16 $di/dt 200A/\mu s$
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery During $t_b$	—	180	—		
		—	120	—		



**Fig. 1 - Typical Load Current vs. Frequency**  
(Load Current =  $I_{RMS}$  of fundamental)

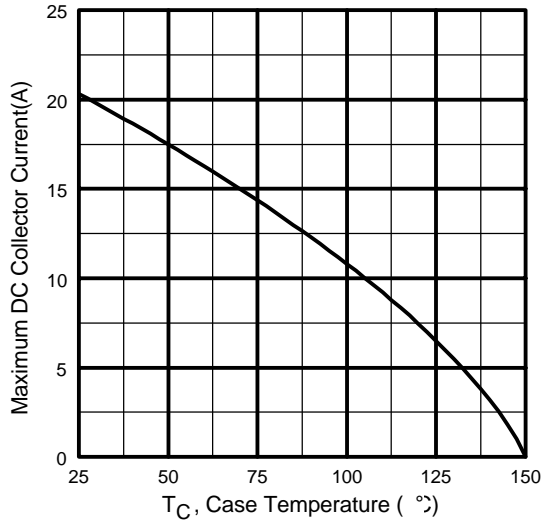


**Fig. 2 - Typical Output Characteristics**  
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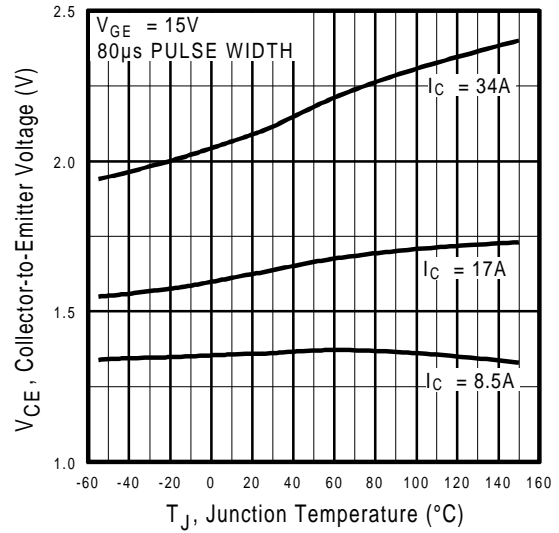


**Fig. 3 - Typical Transfer Characteristics**

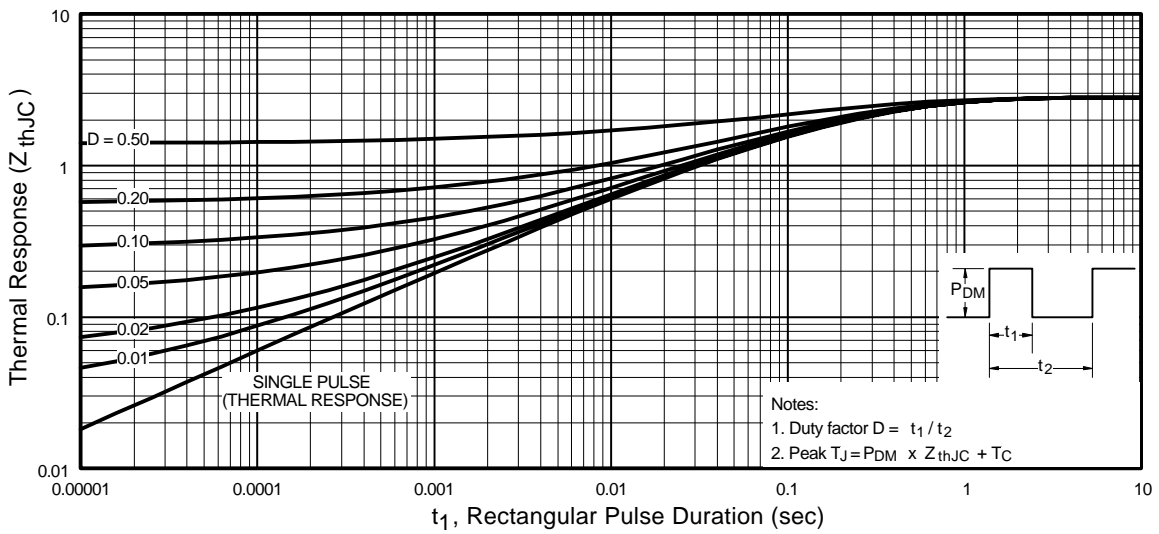
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**Fig. 4** - Maximum Collector Current vs. Case Temperature



**Fig. 5** - Typical Collector-to-Emitter Voltage vs. Junction Temperature



**Fig. 6** - Maximum Effective Transient Thermal Impedance, Junction-to-Case

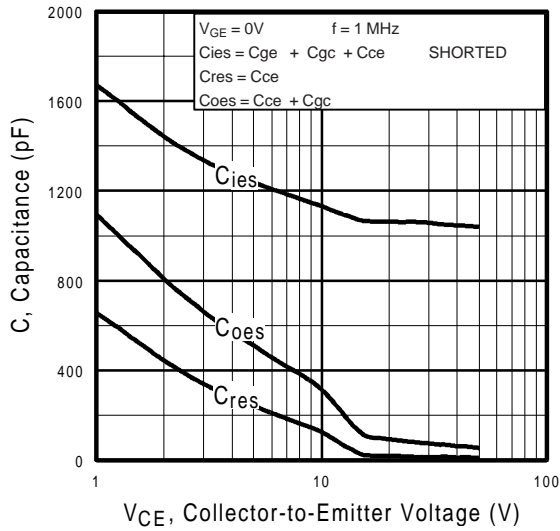


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

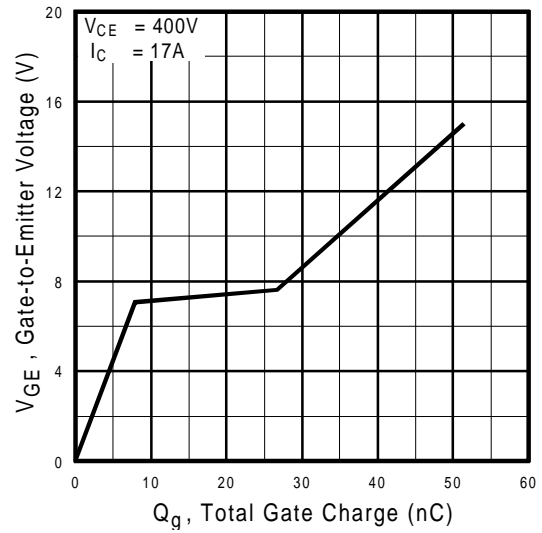


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

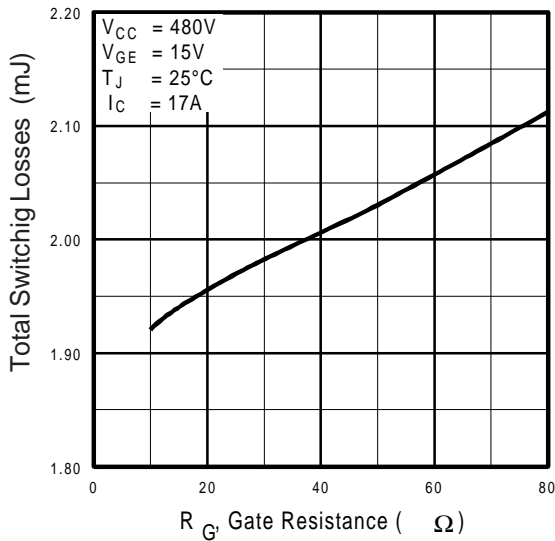


Fig. 9 - Typical Switching Losses vs. Gate Resistance

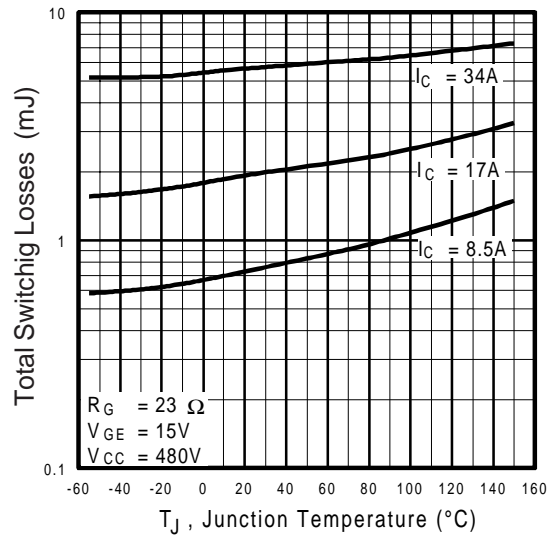
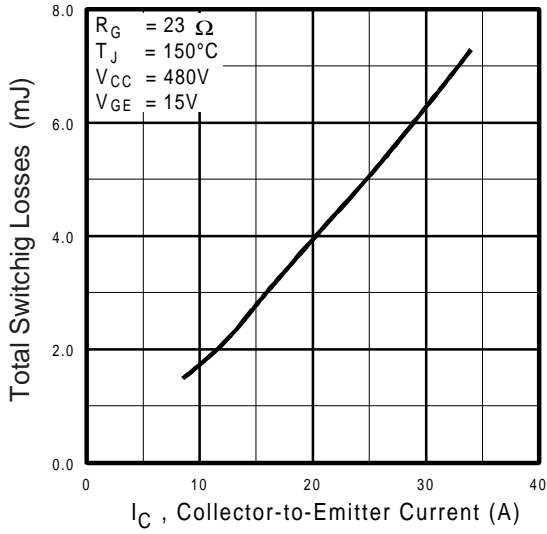
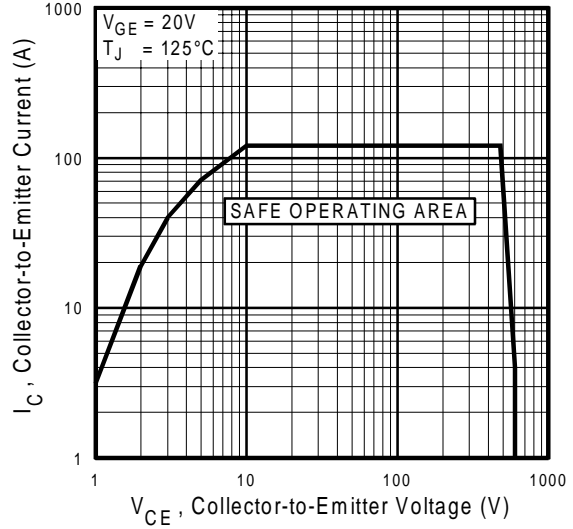


Fig. 10 - Typical Switching Losses vs. Junction Temperature

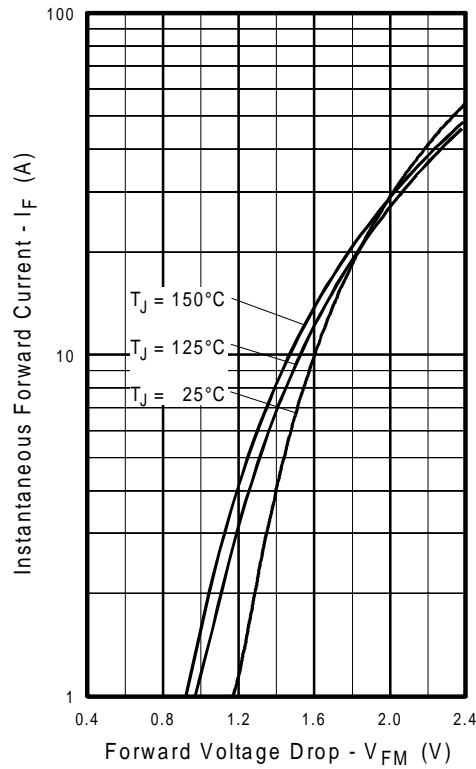
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**Fig. 11** - Typical Switching Losses vs. Collector-to-Emitter Current



**Fig. 12** - Turn-Off SOA



**Fig. 13** - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

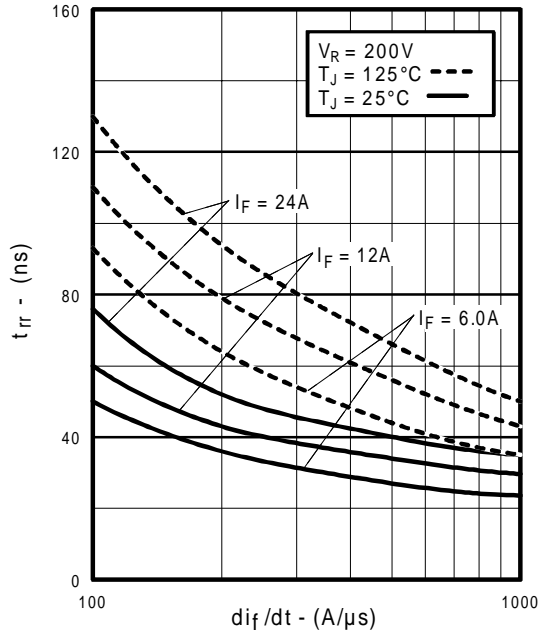


Fig. 14 - Typical Reverse Recovery vs.  $di_f/dt$

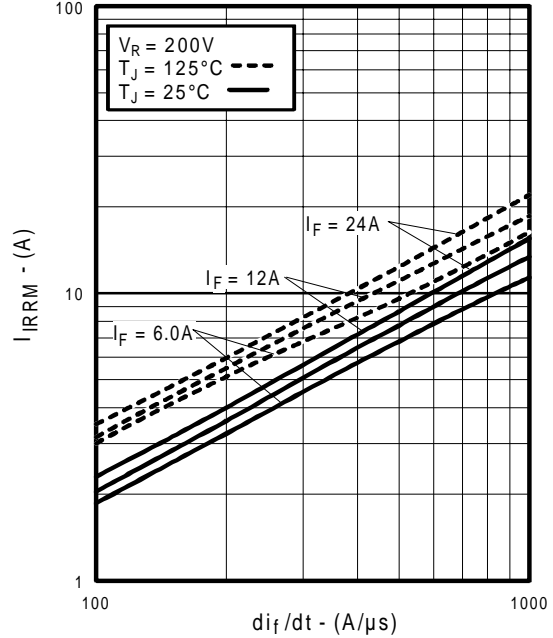


Fig. 15 - Typical Recovery Current vs.  $di_f/dt$

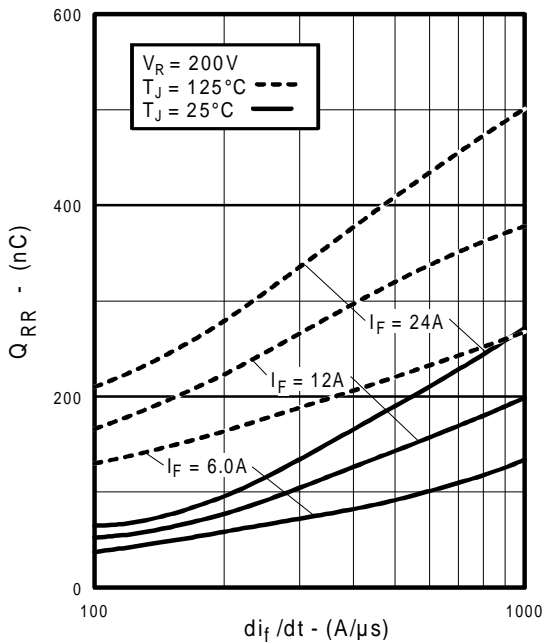


Fig. 16 - Typical Stored Charge vs.  $di_f/dt$

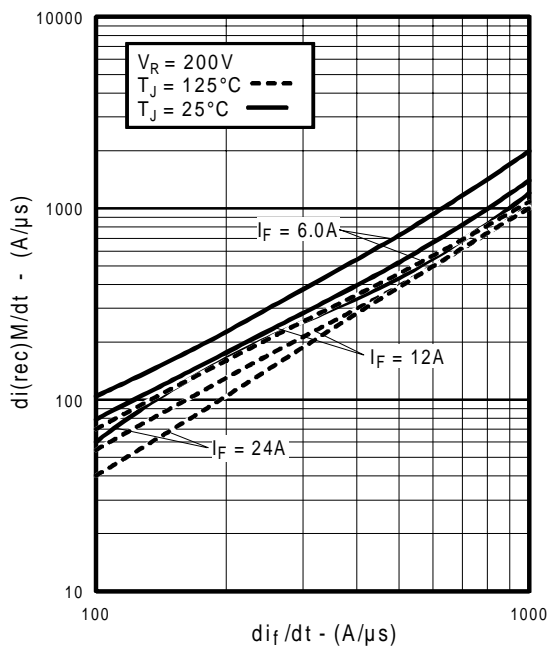
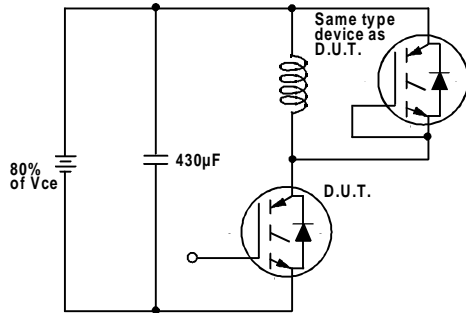
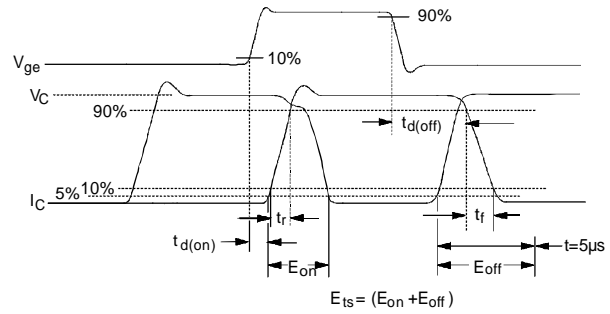


Fig. 17 - Typical  $di_{(rec)M}/dt$  vs.  $di_f/dt$

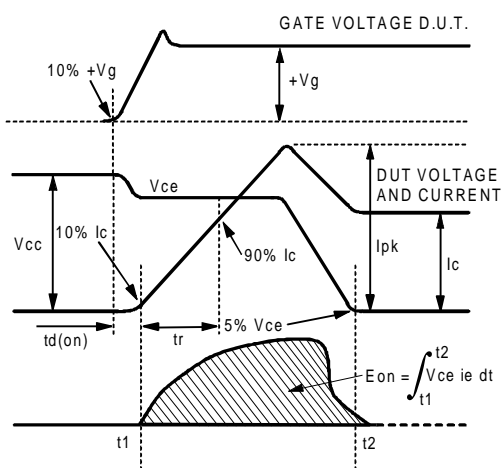
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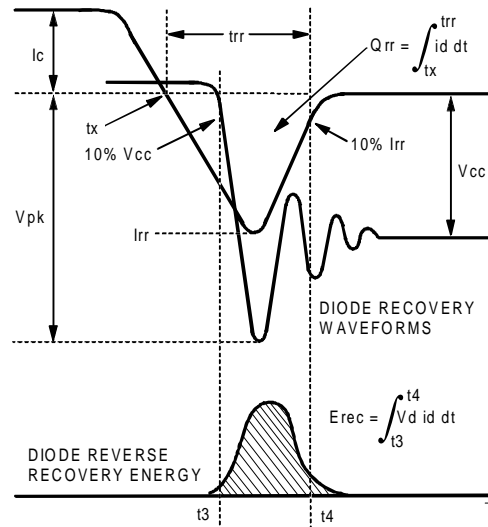
**Fig. 18a** - Test Circuit for Measurement of  $I_{LM}$ ,  $E_{on}$ ,  $E_{off}$ (diode),  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$ ,  $t_{d(on)}$ ,  $t_r$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18b** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{off}$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18c** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{on}$ ,  $t_{d(on)}$ ,  $t_r$



**Fig. 18d** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{rec}$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$



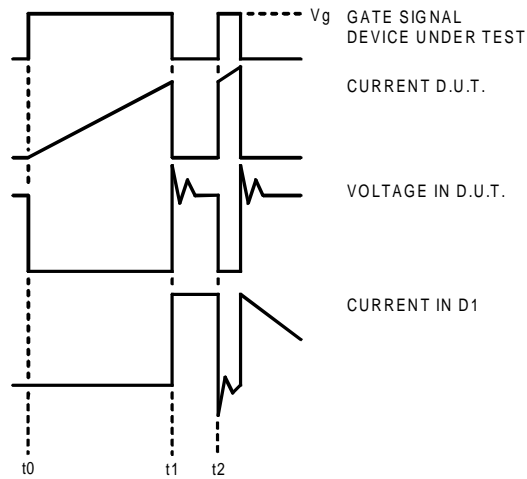


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

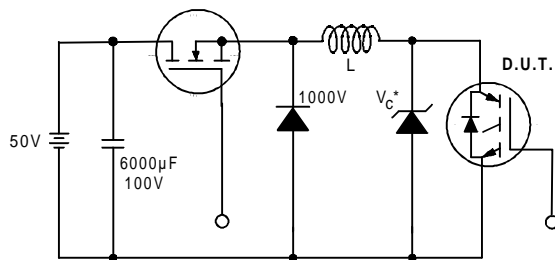


Figure 19. Clamped Inductive Load Test Circuit

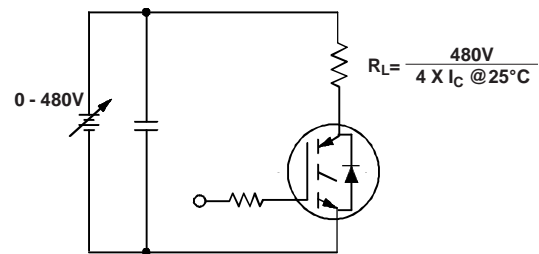


Figure 20. Pulsed Collector Current Test Circuit

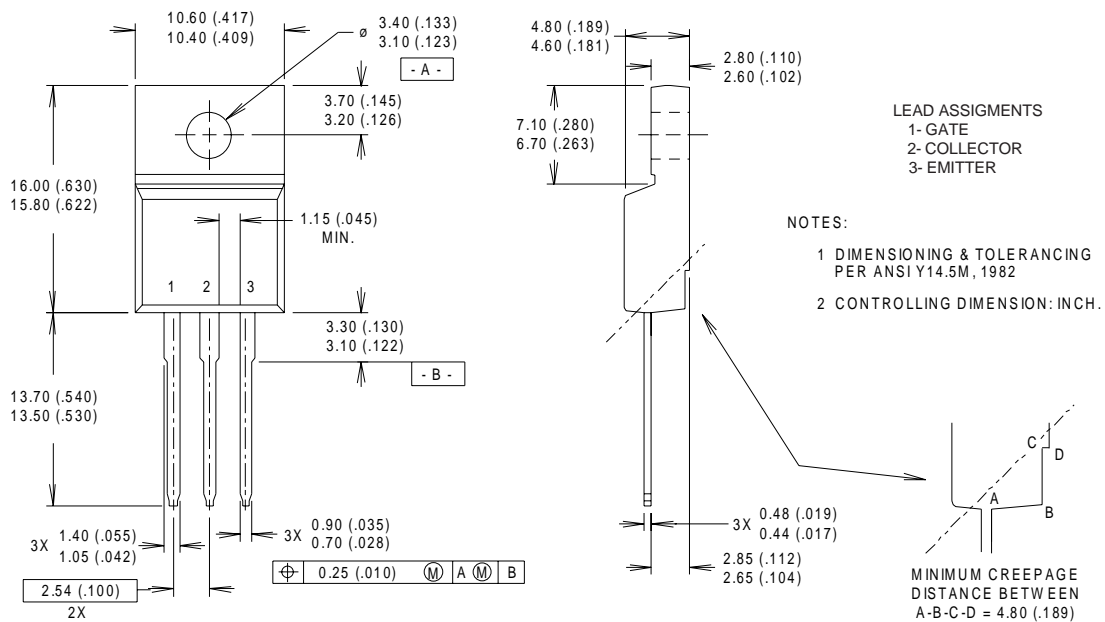
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International  
**IR** Rectifier

## Notes:

- ① Repetitive rating:  $V_{GE}=20V$ ; pulse width limited by maximum junction temperature (figure 20)
- ②  $V_{CC}=80\%(V_{CES})$ ,  $V_{GE}=20V$ ,  $L=10\mu H$ ,  $R_G = 23\Omega$  (figure 19)
- ③ Pulse width  $\leq 80\mu s$ ; duty factor  $\leq 0.1\%$ .
- ④ Pulse width  $5.0\mu s$ , single shot.
- ⑤  $t = 60s$ ,  $f = 60Hz$

## Case Outline — TO-220 FULLPAK



International  
**IR** Rectifier

**WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, Tel: (310) 322 3331

**IR GREAT BRITAIN:** Hurst Green, Oxted, Surrey RH8 9BB, UK Tel: ++ 44 1883 732020

**IR CANADA:** 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200

**IR GERMANY:** Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

**IR ITALY:** Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

**IR FAR EAST:** K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo Japan 171 Tel: 81 3 3983 0086

**IR SOUTHEAST ASIA:** 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994 Tel: ++ 65 838 4630

**IR TAIWAN:** 16 Fl. Suite D. 207, Sec. 2, Tun Haw South Road, Taipei, 10673, Taiwan Tel: 886-2-2377-9936

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